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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	HCS12X
Core Size	16-Bit
Speed	40MHz
Connectivity	CANbus, SCI, SPI
Peripherals	LVD, POR, PWM, WDT
Number of I/O	44
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.72V ~ 5.5V
Data Converters	A/D 8x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s12xs64cae

  - Time-out interrupt and peripheral triggers
  - Start of timers can be aligned
- Up to 8 channel x 8-bit or 4 channel x 16-bit Pulse Width Modulator
  - Programmable period and duty cycle per channel
  - Center- or left-aligned outputs
  - Programmable clock select logic with a wide range of frequencies
- Serial Peripheral Interface Module (SPI)
  - Configurable for 8 or 16-bit data size
  - Full-duplex or single-wire bidirectional
  - Double-buffered transmit and receive
  - Master or Slave mode
  - MSB-first or LSB-first shifting
  - Serial clock phase and polarity options
- Two Serial Communication Interfaces (SCI)
  - Full-duplex or single wire operation
  - Standard mark/space non-return-to-zero (NRZ) format
  - Selectable IrDA 1.4 return-to-zero-inverted (RZI) format with programmable pulse widths
  - 13-bit baud rate selection
  - Programmable character length
  - Programmable polarity for transmitter and receiver
  - Receive wakeup on active edge
  - Break detect and transmit collision detect supporting LIN
- On-Chip Voltage Regulator
  - Two parallel, linear voltage regulators with bandgap reference
  - Low-voltage detect (LVD) with low-voltage interrupt (LVI)
  - Power-on reset (POR) circuit
  - Low-voltage reset (LVR)
- Low-power wake-up timer (API)
  - Internal oscillator driving a down counter
  - Trimmable to +/-5% accuracy
  - Time-out periods range from 0.2ms to ~13s with a 0.2ms resolution
- Input/Output
  - Up to 91 general-purpose input/output (I/O) pins depending on the package option and 2 input-only pins
  - Hysteresis and configurable pull up/pull down device on all input pins
  - Configurable drive strength on all output pins
- Package Options
  - 112-pin low-profile quad flat-pack (LQFP)
  - 80-pin quad flat-pack (QFP)

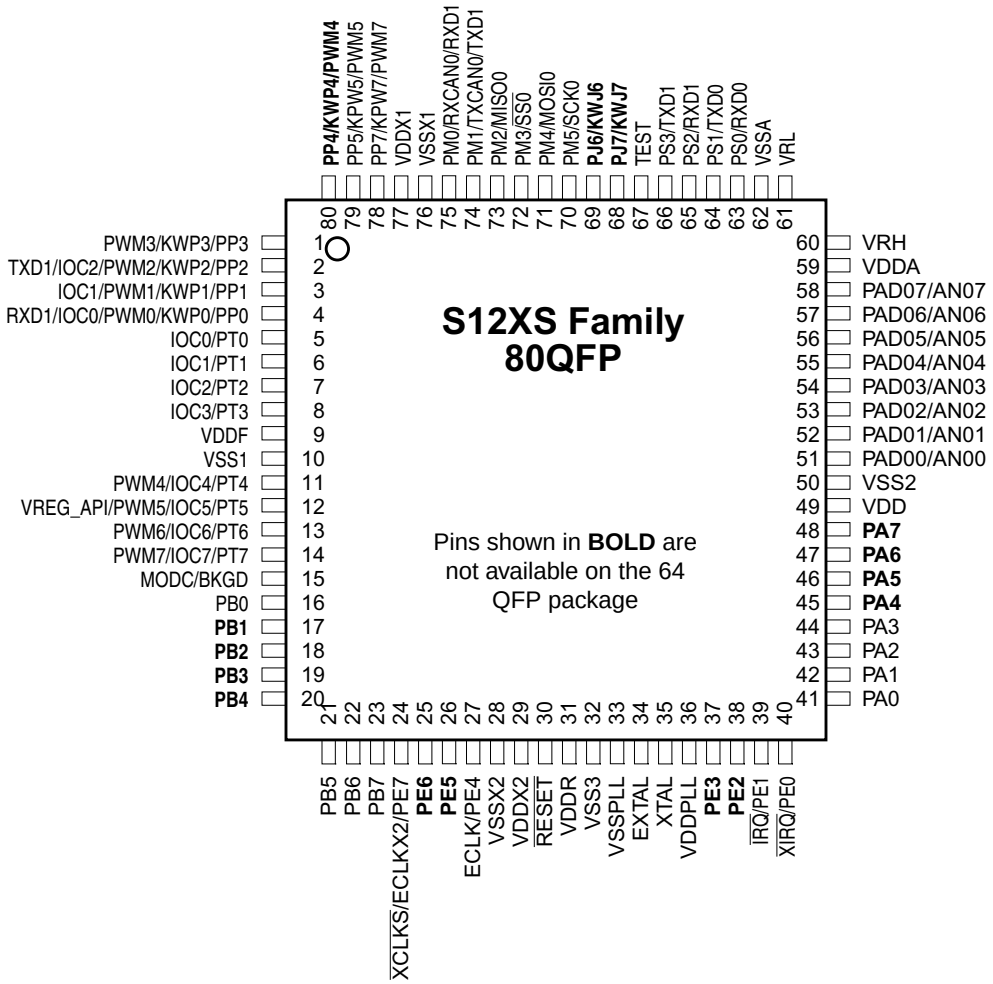


Figure 1-4. S12XS Family Pin Assignments 80-pin QFP Package

Table 2-1. Pin Functions and Priorities (continued)

Port	Pin Name	Pin Function & Priority[1]	I/O	Description	Pin Function after Reset
M	PM[7:6]	GPIO	I/O	General purpose	GPIO
	PM5	(SCK0)	I/O	Serial Peripheral Interface 0 serial clock pin	
		GPIO	I/O	General purpose	
	PM4	(MOSI0)	I/O	Serial Peripheral Interface 0 master out/slave in pin	
		GPIO	I/O	General purpose	
	PM3	($\overline{SS0}$)	I/O	Serial Peripheral Interface 0 slave select output in master mode, input in slave mode or master mode.	
		GPIO	I/O	General purpose	
	PM2	(MISO0)	I/O	Serial Peripheral Interface 0 master in/slave out pin	
		GPIO	I/O	General purpose	
	PM1	TXCAN0	O	MSCAN0 transmit pin	
		(TXD1)	O	Serial Communication Interface 1 transmit pin	
		GPIO	I/O	General purpose	
	PM0	RXCAN0	I	MSCAN0 receive pin	
		(RXD1)	I	Serial Communication Interface 1 receive pin	
		GPIO	I/O	General purpose	

5.4.3 BDM Hardware Commands

Hardware commands are used to read and write target system memory locations and to enter active background debug mode. Target system memory includes all memory that is accessible by the CPU on the SOC which can be on-chip RAM, non-volatile memory (e.g. EEPROM, Flash EEPROM), I/O and control registers, and all external memory.

Hardware commands are executed with minimal or no CPU intervention and do not require the system to be in active BDM for execution, although, they can still be executed in this mode. When executing a hardware command, the BDM sub-block waits for a free bus cycle so that the background access does not disturb the running application program. If a free cycle is not found within 128 clock cycles, the CPU is momentarily frozen so that the BDM can steal a cycle. When the BDM finds a free cycle, the operation does not intrude on normal CPU operation provided that it can be completed in a single cycle. However, if an operation requires multiple cycles the CPU is frozen until the operation is complete, even though the BDM found a free cycle.

The BDM hardware commands are listed in Table 5-6.

The READ_BD and WRITE_BD commands allow access to the BDM register locations. These locations are not normally in the system memory map but share addresses with the application in memory. To distinguish between physical memory locations that share the same address, BDM memory resources are enabled just for the READ_BD and WRITE_BD access cycle. This allows the BDM to access BDM locations unobtrusively, even if the addresses conflict with the application memory map.

Table 5-6. Hardware Commands

Command	Opcode (hex)	Data	Description
BACKGROUND	90	None	Enter background mode if firmware is enabled. If enabled, an ACK will be issued when the part enters active background mode.
ACK_ENABLE	D5	None	Enable Handshake. Issues an ACK pulse after the command is executed.
ACK_DISABLE	D6	None	Disable Handshake. This command does not issue an ACK pulse.
READ_BD_BYTE	E4	16-bit address 16-bit data out	Read from memory with standard BDM firmware lookup table in map. Odd address data on low byte; even address data on high byte.
READ_BD_WORD	EC	16-bit address 16-bit data out	Read from memory with standard BDM firmware lookup table in map. Must be aligned access.
READ_BYTE	E0	16-bit address 16-bit data out	Read from memory with standard BDM firmware lookup table out of map. Odd address data on low byte; even address data on high byte.
READ_WORD	E8	16-bit address 16-bit data out	Read from memory with standard BDM firmware lookup table out of map. Must be aligned access.
WRITE_BD_BYTE	C4	16-bit address 16-bit data in	Write to memory with standard BDM firmware lookup table in map. Odd address data on low byte; even address data on high byte.
WRITE_BD_WORD	CC	16-bit address 16-bit data in	Write to memory with standard BDM firmware lookup table in map. Must be aligned access.
WRITE_BYTE	C0	16-bit address 16-bit data in	Write to memory with standard BDM firmware lookup table out of map. Odd address data on low byte; even address data on high byte.

Table 8-11. RTI Frequency Divide Rates for RTDEC=1

RTR[3:0]	RTR[6:4] =							
	000 ($1x10^3$)	001 ($2x10^3$)	010 ($5x10^3$)	011 ($10x10^3$)	100 ($20x10^3$)	101 ($50x10^3$)	110 ($100x10^3$)	111 ($200x10^3$)
0110 (÷7)	$7x10^3$	$14x10^3$	$35x10^3$	$70x10^3$	$140x10^3$	$350x10^3$	$700x10^3$	$1.4x10^6$
0111 (÷8)	$8x10^3$	$16x10^3$	$40x10^3$	$80x10^3$	$160x10^3$	$400x10^3$	$800x10^3$	$1.6x10^6$
1000 (÷9)	$9x10^3$	$18x10^3$	$45x10^3$	$90x10^3$	$180x10^3$	$450x10^3$	$900x10^3$	$1.8x10^6$
1001 (÷10)	$10 x10^3$	$20x10^3$	$50x10^3$	$100x10^3$	$200x10^3$	$500x10^3$	$1x10^6$	$2x10^6$
1010 (÷11)	$11 x10^3$	$22x10^3$	$55x10^3$	$110x10^3$	$220x10^3$	$550x10^3$	$1.1x10^6$	$2.2x10^6$
1011 (÷12)	$12x10^3$	$24x10^3$	$60x10^3$	$120x10^3$	$240x10^3$	$600x10^3$	$1.2x10^6$	$2.4x10^6$
1100 (÷13)	$13x10^3$	$26x10^3$	$65x10^3$	$130x10^3$	$260x10^3$	$650x10^3$	$1.3x10^6$	$2.6x10^6$
1101 (÷14)	$14x10^3$	$28x10^3$	$70x10^3$	$140x10^3$	$280x10^3$	$700x10^3$	$1.4x10^6$	$2.8x10^6$
1110 (÷15)	$15x10^3$	$30x10^3$	$75x10^3$	$150x10^3$	$300x10^3$	$750x10^3$	$1.5x10^6$	$3x10^6$
1111 (÷16)	$16x10^3$	$32x10^3$	$80x10^3$	$160x10^3$	$320x10^3$	$800x10^3$	$1.6x10^6$	$3.2x10^6$

8.3.2.9 S12XECRG COP Control Register (COPCTL)

This register controls the COP (Computer Operating Properly) watchdog.

Module Base + 0x0008

	7	6	5	4	3	2	1	0
R	WCOP	RSBCK	0	0	0	CR2	CR1	CR0
W			WRTMASK					
Reset[1]	0	0	0	0	0	0	0	0

1. Refer to Device User Guide (Section: S12XECRG) for reset values of WCOP, CR2, CR1 and CR0.

= Unimplemented or Reserved

Figure 8-11. S12XECRG COP Control Register (COPCTL)

Read: Anytime

Write:

1. RSBCK: anytime in special modes; write to “1” but not to “0” in all other modes
2. WCOP, CR2, CR1, CR0:
   - — Anytime in special modes
   - — Write once in all other modes
     - – Writing CR[2:0] to “000” has no effect, but counts for the “write once” condition.
     - – Writing WCOP to “0” has no effect, but counts for the “write once” condition.

Write: Anytime (any value written causes PWM counter to be reset to $00).

13.3.2.13 PWM Channel Period Registers (PWMPERx)

There is a dedicated period register for each channel. The value in this register determines the period of the associated PWM channel.

The period registers for each channel are double buffered so that if they change while the channel is enabled, the change will NOT take effect until one of the following occurs:

- The effective period ends
- The counter is written (counter resets to $00)
- The channel is disabled

In this way, the output of the PWM will always be either the old waveform or the new waveform, not some variation in between. If the channel is not enabled, then writes to the period register will go directly to the latches as well as the buffer.

NOTE

Reads of this register return the most recent value written. Reads do not necessarily return the value of the currently active period due to the double buffering scheme.

See Section 13.4.2.3, “PWM Period and Duty” for more information.

To calculate the output period, take the selected clock source period for the channel of interest (A, B, SA, or SB) and multiply it by the value in the period register for that channel:

- Left aligned output (CAEx = 0)
- PWMx Period = Channel Clock Period * PWMPERx Center Aligned Output (CAEx = 1)

  PWMx Period = Channel Clock Period * (2 * PWMPERx)

For boundary case programming values, please refer to Section 13.4.2.8, “PWM Boundary Cases”.

Module Base + 0x0014 = PWMPER0, 0x0015 = PWMPER1, 0x0016 = PWMPER2, 0x0017 = PWMPER3
Module Base + 0x0018 = PWMPER4, 0x0019 = PWMPER5, 0x001A = PWMPER6, 0x001B = PWMPER7

	7	6	5	4	3	2	1	0
R W	Bit 7	6	5	4	3	2	1	Bit 0
Reset	1	1	1	1	1	1	1	1

Figure 13-15. PWM Channel Period Registers (PWMPERx)

Read: Anytime

Write: Anytime

14.4.5 Transmitter

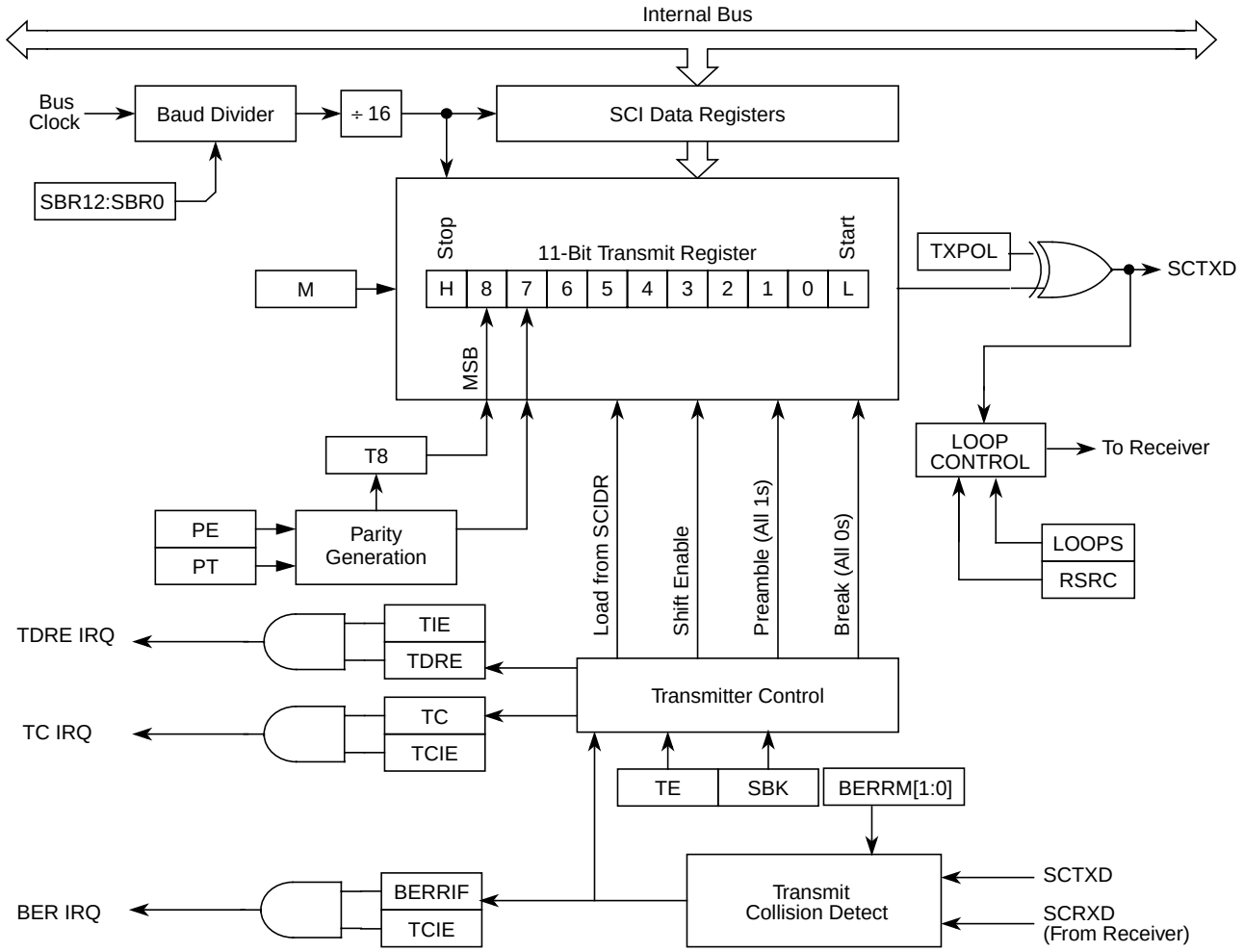


Figure 14-16. Transmitter Block Diagram

14.4.5.1 Transmitter Character Length

The SCI transmitter can accommodate either 8-bit or 9-bit data characters. The state of the M bit in SCI control register 1 (SCICR1) determines the length of data characters. When transmitting 9-bit data, bit T8 in SCI data register high (SCIDRH) is the ninth bit (bit 8).

14.4.5.2 Character Transmission

To transmit data, the MCU writes the data bits to the SCI data registers (SCIDRH/SCIDRL), which in turn are transferred to the transmitter shift register. The transmit shift register then shifts a frame out through the TXD pin, after it has prefaced them with a start bit and appended them with a stop bit. The SCI data registers (SCIDRH and SCIDRL) are the write-only buffers between the internal data bus and the transmit shift register.

14.4.6 Receiver

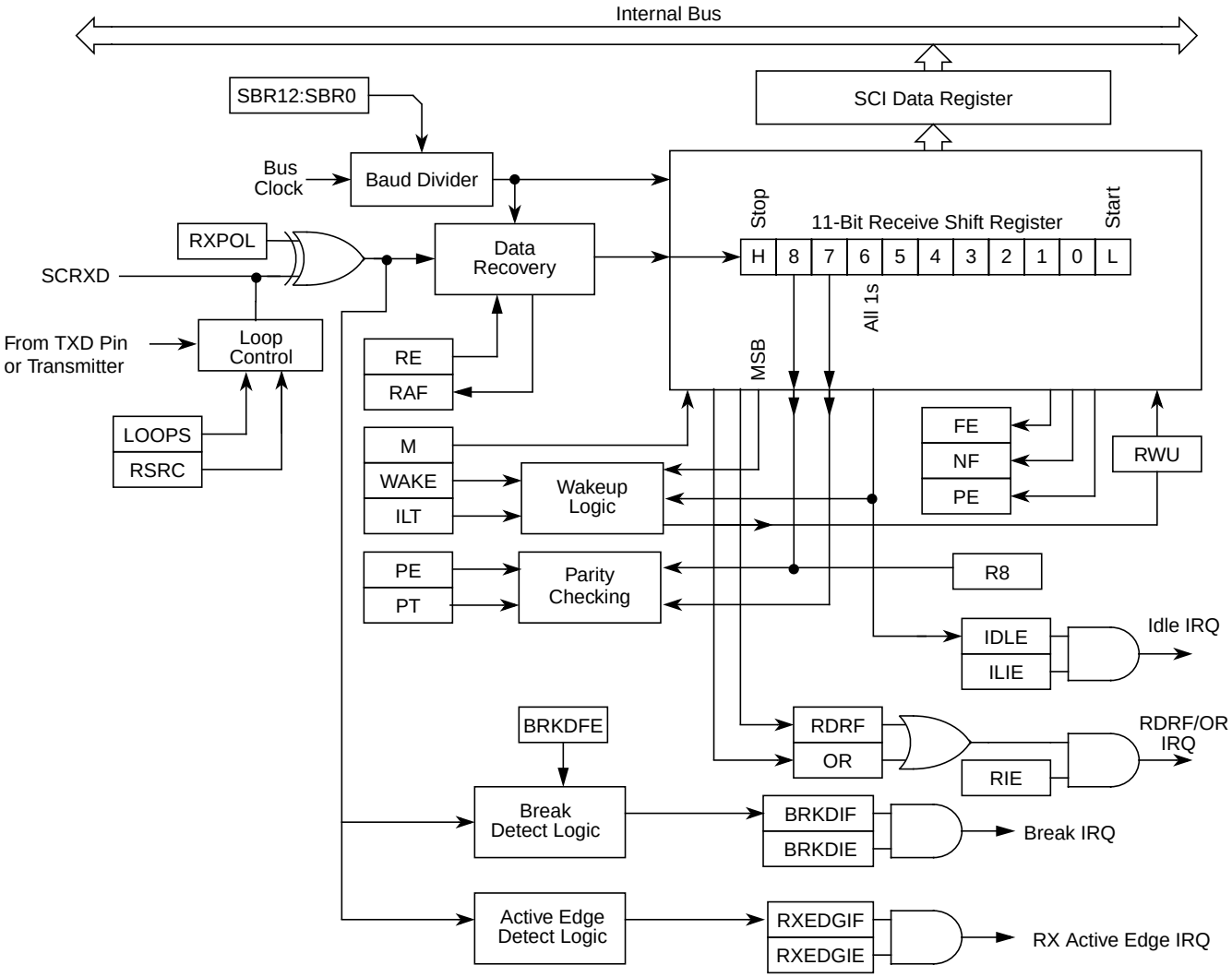


Figure 14-20. SCI Receiver Block Diagram

14.4.6.1 Receiver Character Length

The SCI receiver can accommodate either 8-bit or 9-bit data characters. The state of the M bit in SCI control register 1 (SCICR1) determines the length of data characters. When receiving 9-bit data, bit R8 in SCI data register high (SCIDRH) is the ninth bit (bit 8).

14.4.6.2 Character Reception

During an SCI reception, the receive shift register shifts a frame in from the RXD pin. The SCI data register is the read-only buffer between the internal data bus and the receive shift register.

After a complete frame shifts into the receive shift register, the data portion of the frame transfers to the SCI data register. The receive data register full flag, RDRF, in SCI status register 1 (SCISR1) becomes set,

To determine the value of a data bit and to detect noise, recovery logic takes samples at RT8, RT9, and RT10. Table 14-18 summarizes the results of the data bit samples.

Table 14-18. Data Bit Recovery

RT8, RT9, and RT10 Samples	Data Bit Determination	Noise Flag
000	0	0
001	0	1
010	0	1
011	1	1
100	0	1
101	1	1
110	1	1
111	1	0

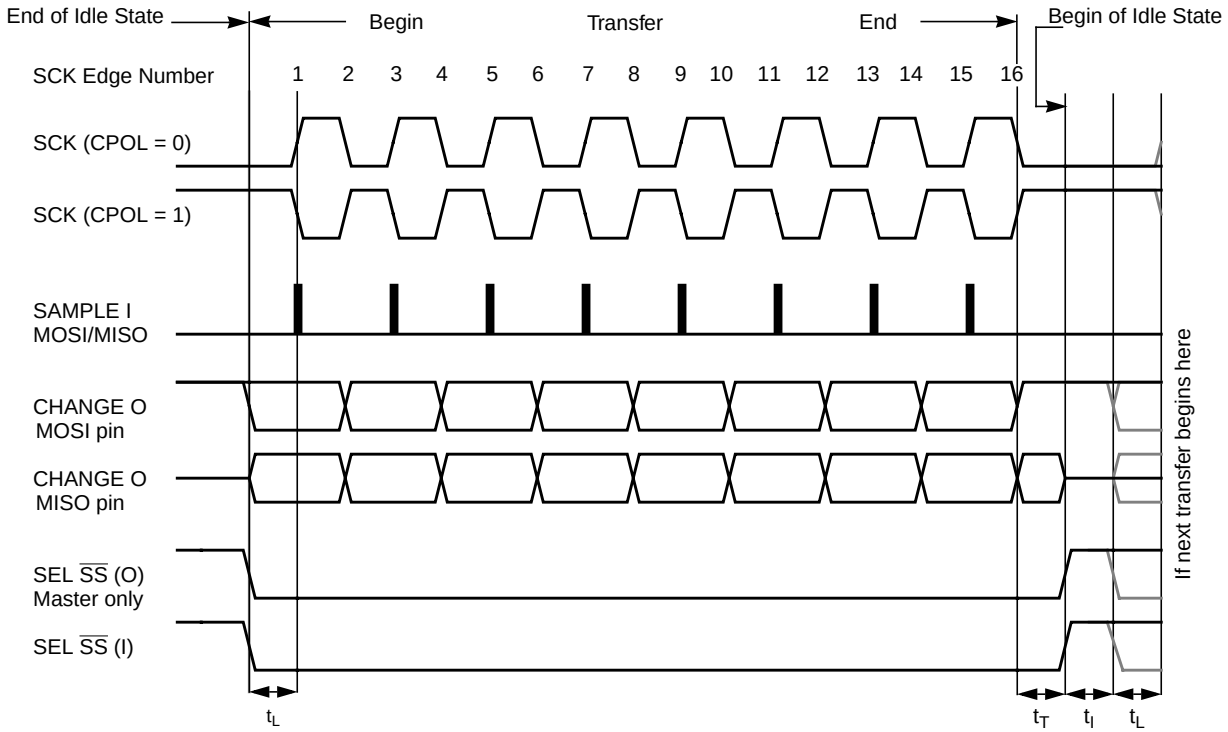
NOTE

The RT8, RT9, and RT10 samples do not affect start bit verification. If any or all of the RT8, RT9, and RT10 start bit samples are logic 1s following a successful start bit verification, the noise flag (NF) is set and the receiver assumes that the bit is a start bit (logic 0).

To verify a stop bit and to detect noise, recovery logic takes samples at RT8, RT9, and RT10. Table 14-19 summarizes the results of the stop bit samples.

Table 14-19. Stop Bit Recovery

RT8, RT9, and RT10 Samples	Framing Error Flag	Noise Flag
000	1	0
001	1	1
010	1	1
011	0	1
100	1	1
101	0	1
110	0	1
111	0	0



t_L = Minimum leading time before the first SCK edge

t_T = Minimum trailing time after the last SCK edge

t_I = Minimum idling time between transfers (minimum $\overline{SS}$ high time)

t_L, t_T, and t_I are guaranteed for the master mode and required for the slave mode.

Figure 15-12. SPI Clock Format 0 (CPHA = 0), with 8-bit Transfer Width selected (XFRW = 0)

17.4.11.1 Low-Voltage Interrupt (LVI)

In FPM, VREG_3V3 monitors the input voltage V_{DDA}. Whenever V_{DDA} drops below level $V_{LVIA,}$ the status bit LVDS is set to 1. On the other hand, LVDS is reset to 0 when V_{DDA} rises above level V_{LVID}. An interrupt, indicated by flag LVIF = 1, is triggered by any change of the status bit LVDS if interrupt enable bit LVIE = 1.

NOTE

On entering the Reduced Power Mode, the LVIF is not cleared by the VREG_3V3.

17.4.11.2 HTI - High Temperature Interrupt

In FPM VREG monitors the die temperature T_{DIE}. Whenever T_{DIE} exceeds level T_{HTIA} the status bit HTDS is set to 1. Vice versa, HTDS is reset to 0 when T_{DIE} get below level T_{HTID}. An interrupt, indicated by flag HTIF=1, is triggered by any change of the status bit HTDS if interrupt enable bit HTIE=1.

NOTE

On entering the Reduced Power Mode the HTIF is not cleared by the VREG.

17.4.11.3 Autonomous Periodical Interrupt (API)

As soon as the configured timeout period of the API has elapsed, the APIF bit is set. An interrupt, indicated by flag APIF = 1, is triggered if interrupt enable bit APIE = 1.

18.3.2.2 Flash Security Register (FSEC)

The FSEC register holds all bits associated with the security of the MCU and Flash module.

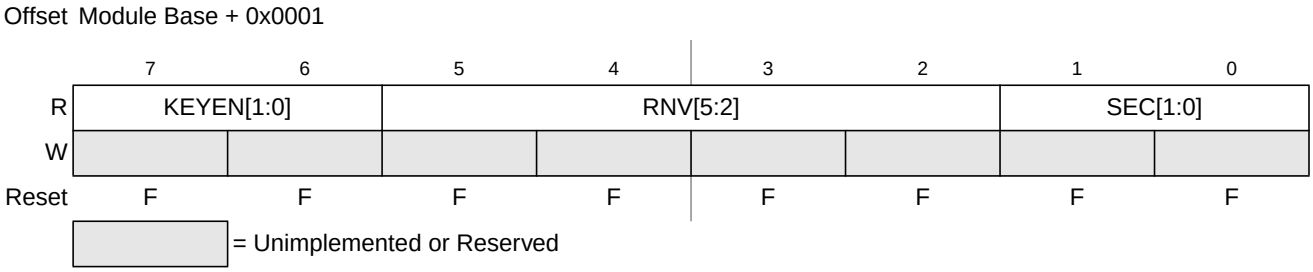


Figure 18-6. Flash Security Register (FSEC)

All bits in the FSEC register are readable but not writable.

During the reset sequence, the FSEC register is loaded with the contents of the Flash security byte in the Flash configuration field at global address 0x7F_FF0F located in P-Flash memory (see Table 18-3) as indicated by reset condition F in Figure 18-6. If a double bit fault is detected while reading the P-Flash phrase containing the Flash security byte during the reset sequence, all bits in the FSEC register will be set to leave the Flash module in a secured state with backdoor key access disabled.

Table 18-8. FSEC Field Descriptions

Field	Description
7–6 KEYEN[1:0]	**Backdoor Key Security Enable Bits** — The KEYEN[1:0] bits define the enabling of backdoor key access to the Flash module as shown in Table 18-9.
5–2 RNV[5:2}	**Reserved Nonvolatile Bits** — The RNV bits should remain in the erased state for future enhancements.
1–0 SEC[1:0]	**Flash Security Bits** — The SEC[1:0] bits define the security state of the MCU as shown in Table 18-10. If the Flash module is unsecured using backdoor key access, the SEC bits are forced to 10.

Table 18-9. Flash KEYEN States

KEYEN[1:0]	Status of Backdoor Key Access
00	DISABLED
01	DISABLED[1]
10	ENABLED
11	DISABLED

1 Preferred KEYEN state to disable backdoor key access.

Table 18-10. Flash Security States

SEC[1:0]	Status of Security
00	SECURED
01	SECURED[1]
10	UNSECURED
11	SECURED

keys stored in the Flash memory via the Memory Controller. If the keys presented in the Verify Backdoor Access Key command match the backdoor keys stored in the Flash memory, the SEC bits in the FSEC register (see Table 18-10) will be changed to unsecure the MCU. Key values of 0x0000 and 0xFFFF are not permitted as backdoor keys. While the Verify Backdoor Access Key command is active, P-Flash block 0 will not be available for read access and will return invalid data.

The user code stored in the P-Flash memory must have a method of receiving the backdoor keys from an external stimulus. This external stimulus would typically be through one of the on-chip serial ports.

If the KEYEN[1:0] bits are in the enabled state (see Section 18.3.2.2), the MCU can be unsecured by the backdoor key access sequence described below:

1. Follow the command sequence for the Verify Backdoor Access Key command as explained in Section 18.4.2.11
2. If the Verify Backdoor Access Key command is successful, the MCU is unsecured and the SEC[1:0] bits in the FSEC register are forced to the unsecure state of 10

The Verify Backdoor Access Key command is monitored by the Memory Controller and an illegal key will prohibit future use of the Verify Backdoor Access Key command. A reset of the MCU is the only method to re-enable the Verify Backdoor Access Key command.

After the backdoor keys have been correctly matched, the MCU will be unsecured. After the MCU is unsecured, the sector containing the Flash security byte can be erased and the Flash security byte can be reprogrammed to the unsecure state, if desired.

In the unsecure state, the user has full control of the contents of the backdoor keys by programming addresses 0x7F_FF00–0x7F_FF07 in the Flash configuration field.

The security as defined in the Flash security byte (0x7F_FF0F) is not changed by using the Verify Backdoor Access Key command sequence. The backdoor keys stored in addresses 0x7F_FF00–0x7F_FF07 are unaffected by the Verify Backdoor Access Key command sequence. After the next reset of the MCU, the security state of the Flash module is determined by the Flash security byte (0x7F_FF0F). The Verify Backdoor Access Key command sequence has no effect on the program and erase protections defined in the Flash protection register, FPROT.

18.5.2 Unsecuring the MCU in Special Single Chip Mode using BDM

The MCU can be unsecured in special single chip mode by erasing the P-Flash and D-Flash memory by one of the following methods:

- Reset the MCU into special single chip mode, delay while the erase test is performed by the BDM, send BDM commands to disable protection in the P-Flash and D-Flash memory, and execute the Erase All Blocks command write sequence to erase the P-Flash and D-Flash memory.
- Reset the MCU into special expanded wide mode, disable protection in the P-Flash and D-Flash memory and run code from external memory to execute the Erase All Blocks command write sequence to erase the P-Flash and D-Flash memory.

After the CCIF flag sets to indicate that the Erase All Blocks operation has completed, reset the MCU into special single chip mode. The BDM will execute the Erase Verify All Blocks command write sequence to verify that the P-Flash and D-Flash memory is erased. If the P-Flash and D-Flash memory are verified as

Table 19-45. Erase Flash Block Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x09	Global address [22:16] to identify Flash block
001	Global address [15:0] in Flash block to be erased	

Upon clearing CCIF to launch the Erase Flash Block command, the Memory Controller will erase the selected Flash block and verify that it is erased. The CCIF flag will set after the Erase Flash Block operation has completed.

Table 19-46. Erase Flash Block Command Error Handling

Register	Error Bit	Error Condition
FSTAT	ACCERR	Set if CCOBIX[2:0] != 001 at command launch
		Set if command not available in current mode (see Table 19-28)
		Set if an invalid global address [22:16] is supplied
		Set if the supplied P-Flash address is not phrase-aligned or if the D-Flash address is not word-aligned
	FPVIOL	Set if an area of the selected Flash block is protected
	MGSTAT1	Set if any errors have been encountered during the verify operation
	MGSTAT0	Set if any non-correctable errors have been encountered during the verify operation

19.4.2.9 Erase P-Flash Sector Command

The Erase P-Flash Sector operation will erase all addresses in a P-Flash sector.

Table 19-47. Erase P-Flash Sector Command FCCOB Requirements

CCOBIX[2:0]	FCCOB Parameters	
000	0x0A	Global address [22:16] to identify P-Flash block to be erased
001	Global address [15:0] anywhere within the sector to be erased. Refer to Section 19.1.2.1 for the P-Flash sector size.	

Upon clearing CCIF to launch the Erase P-Flash Sector command, the Memory Controller will erase the selected Flash sector and then verify that it is erased. The CCIF flag will be set after the Erase P-Flash Sector operation has completed.

Table 20-29. P-Flash Commands

FCMD	Command	Function on P-Flash Memory
0x01	Erase Verify All Blocks	Verify that all P-Flash (and D-Flash) blocks are erased.
0x02	Erase Verify Block	Verify that a P-Flash block is erased.
0x03	Erase Verify P-Flash Section	Verify that a given number of words starting at the address provided are erased.
0x04	Read Once	Read a dedicated 64 byte field in the nonvolatile information register in P-Flash block 0 that was previously programmed using the Program Once command.
0x06	Program P-Flash	Program a phrase in a P-Flash block.
0x07	Program Once	Program a dedicated 64 byte field in the nonvolatile information register in P-Flash block 0 that is allowed to be programmed only once.
0x08	Erase All Blocks	Erase all P-Flash (and D-Flash) blocks. An erase of all Flash blocks is only possible when the FPLDIS, FPHDIS, and FPOPEN bits in the FPROT register and the DPOPEN bit in the DFPROT register are set prior to launching the command.
0x09	Erase Flash Block	Erase a P-Flash (or D-Flash) block. An erase of the full P-Flash block is only possible when FPLDIS, FPHDIS and FPOPEN bits in the FPROT register are set prior to launching the command.
0x0A	Erase P-Flash Sector	Erase all bytes in a P-Flash sector.
0x0B	Unsecure Flash	Supports a method of releasing MCU security by erasing all P-Flash (and D-Flash) blocks and verifying that all P-Flash (and D-Flash) blocks are erased.
0x0C	Verify Backdoor Access Key	Supports a method of releasing MCU security by verifying a set of security keys.
0x0D	Set User Margin Level	Specifies a user margin read level for all P-Flash blocks.
0x0E	Set Field Margin Level	Specifies a field margin read level for all P-Flash blocks (special modes only).

20.4.1.5 D-Flash Commands

Table 20-30 summarizes the valid D-Flash commands along with the effects of the commands on the D-Flash block.

Table 20-30. D-Flash Commands

FCMD	Command	Function on D-Flash Memory
0x01	Erase Verify All Blocks	Verify that all D-Flash (and P-Flash) blocks are erased.
0x02	Erase Verify Block	Verify that the D-Flash block is erased.
0x08	Erase All Blocks	Erase all D-Flash (and P-Flash) blocks. An erase of all Flash blocks is only possible when the FPLDIS, FPHDIS, and FPOPEN bits in the FPROT register and the DPOPEN bit in the DFPROT register are set prior to launching the command.
0x09	Erase Flash Block	Erase a D-Flash (or P-Flash) block. An erase of the full D-Flash block is only possible when DPOPEN bit in the DFPROT register is set prior to launching the command.

The VDDX, VSSX pin pairs [2:1] supply the I/O pins.

VDDR supplies the internal voltage regulator.

VDDPLL, VSSPLL pin pair supply the oscillator and the PLL.

VSS1, VSS2 and VSS3 are internally connected by metal.

All VDDX pins are internally connected by metal.

All VSSX pins are internally connected by metal.

VDDA is connected to all VDDX pins by diodes for ESD protection such that VDDX must not exceed VDDA by more than a diode voltage drop. VDDA can exceed VDDX by more than a diode drop in order to support applications with a 5V A/D converter range and 3.3V I/O pin range.

VSSA and VSSX are connected by anti-parallel diodes for ESD protection.

NOTE

In the following context V_{DD35} is used for either VDDA, VDDR, and VDDX; V_{SS35} is used for either VSSA and VSSX unless otherwise noted.

I_{DD35} denotes the sum of the currents flowing into the VDDA and VDDR pins. The Run mode current in the VDDX domain is external load dependent.

V_{DD} is used for VDD, V_{SS} is used for VSS1, VSS2 and VSS3.

V_{DDPLL} is used for VDDPLL, V_{SSPLL} is used for VSSPLL

I_{DD} is used for the sum of the currents flowing into VDD, VDDF and VDDPLL.

A.1.3 Pins

There are four groups of functional pins.

A.1.3.1 I/O Pins

The I/O pins have a level in the range of 3.13V to 5.5V. This class of pins is comprised of all port I/O pins, the analog inputs, BKGD and the $\overline{\text{RESET}}$ pins. Some functionality may be disabled. For example the BKGD pin pull up is always enabled.

A.1.3.2 Analog Reference

This group is made up by the V_{RH} and V_{RL} pins.

A.1.3.3 Oscillator

The pins EXTAL, XTAL dedicated to the oscillator have a nominal 1.8V level. They are supplied by VDDPLL.

Table A-5. Thermal Package Characteristics (9S12XS256)[1]

Num	C	Rating	Symbol	Min	Typ	Max	Unit
LQFP 112							
1	D	Thermal resistance LQFP 112, single sided PCB[2]	θ_{JA}	—	—	62	°C/W
2	D	Thermal resistance LQFP 112, double sided PCB with 2 internal planes[3]	θ_{JA}	—	—	51	°C/W
3	D	Junction to Board LQFP 112	θ_{JB}	—	—	39	°C/W
4	D	Junction to Case LQFP 112[4]	θ_{JC}	—	—	16	°C/W
5	D	Junction to Package Top LQFP 112[5]	Ψ_{JT}	—	—	3	°C/W
QFP 80							
6	D	Thermal resistance QFP 80, single sided PCB[2]	θ_{JA}	—	—	57	°C/W
7	D	Thermal resistance QFP 80, double sided PCB with 2 internal planes[3]	θ_{JA}	—	—	45	°C/W
8	D	Junction to Board QFP 80	θ_{JB}	—	—	29	°C/W
9	D	Junction to Case QFP 80[4]	θ_{JC}	—	—	20	°C/W
10	D	Junction to Package Top QFP 80[5]	Ψ_{JT}	—	—	5	°C/W
LQFP 64							
11	D	Thermal resistance LQFP 64, single sided PCB[2]	θ_{JA}	—	—	68	°C/W
12	D	Thermal resistance LQFP 64, double sided PCB with 2 internal planes[3]	θ_{JA}	—	—	50	°C/W
13	D	Junction to Board LQFP 64	θ_{JB}	—	—	32	°C/W
14	D	Junction to Case LQFP 64[4]	θ_{JC}	—	—	15	°C/W
15	D	Junction to Package Top LQFP 64[5]	Ψ_{JT}	—	—	3	°C/W

1 The values for thermal resistance are achieved by package simulations

2 Junction to ambient thermal resistance, θ_{JA} was simulated to be equivalent to the JEDEC specification JESD51-2 in a horizontal configuration in natural convection.

3 Junction to ambient thermal resistance, θ_{JA} was simulated to be equivalent to the JEDEC specification JESD51-7 in a horizontal configuration in natural convection.

4 Junction to case thermal resistance was simulated to be equivalent to the measured values using the cold plate technique with the cold plate temperature used as the “case” temperature. This basic cold plate measurement technique is described by MIL-STD 883D, Method 1012.1. This is the correct thermal metric to use to calculate thermal performance when the package is being used with a heat sink.

5 Thermal characterization parameter Ψ_{JT} is the “resistance” from junction to reference point thermocouple on top center of the case as defined in JESD51-2. Ψ_{JT} is a useful value to use to estimate junction temperature in a steady state customer enviroment.

Table A-18. NVM Timing Characteristics

Conditions are as shown in Table A-4, with 40MHz bus and f_{NVMOP}= 1MHz unless otherwise noted.							
Num	**C**	**Rating**	**Symbol**	**Min**	**Typ**	**Max**	**Unit**
1	D	External oscillator clock	f_{NVMOSC}	2	—	40[1]	MHz
2	D	Bus frequency for programming or erase operations	f_{NVMBUS}	1	—	40	MHz
3	D	Operating frequency	f_{NVMOP}	800	—	1050	kHz
4	D	P-Flash phrase programming	t_{bwpgm}	—	171	183	µs
6	P	P-Flash sector erase time	t_{era}	—	20	21	ms
7	P	Erase All Blocks (Mass erase) time	t_{mass}	—	101	102	ms
7a	D	Unsecure Flash	t_{uns}	—	101	102	ms
8	D	P-Flash erase verify (blank check) time[2]	t_{check}	—	—	33500[2]	t_{cyc}
9a	D	D-Flash word programming 1 word	t_{dpgm}	—	97	104	µs
9b	D	D-Flash word programming 2 words	t_{dpgm}	—	167	181	µs
9c	D	D-Flash word programming 3 words	t_{dpgm}	—	237	258	µs
9d	D	D-Flash word programming 4 words	t_{dpgm}	—	307	335	µs
9e	D	D-Flash word programming 4 words crossing row boundary	t_{dpgm}	—	335	363	µs
10	D	D-Flash sector erase time	t_{eradf}	—	5.2[3]	21	ms
11	D	D-Flash erase verify (blank check) time	t_{check}	—	—	17500	t_{cyc}

1 Restrictions for oscillator in crystal mode apply.
2 Valid for both “Erase verify all” or “Erase verify block” on 256K block without failing locations
3 This is a typical value for a new device

A.3.2 NVM Reliability Parameters

The reliability of the NVM blocks is guaranteed by stress test during qualification, constant process monitors and burn-in to screen early life failures.

The data retention and program/erase cycling failure rates are specified at the operating conditions noted. The program/erase cycle count on the sector is incremented every time a sector or mass erase event is executed.

The standard shipping condition for both the D-Flash and P-Flash memory is erased with security disabled. However it is recommended that each block or sector is erased before factory programming to ensure that the full data retention capability is achieved. Data retention time is measured from the last erase operation.

0x0240–0x027F Port Integration Module (PIM) Map 5 of 5

Address	Name		Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0x0260	PTH	R	PTH7	PTH6	PTH5	PTH4	PTH3	PTH2	PTH1	PTH0
		W								
0x0261	PTIH	R	PTIH7	PTIH6	PTIH5	PTIH4	PTIH3	PTIH2	PTIH1	PTIH0
		W								
0x0262	DDRH	R	DDRH7	DDRH6	DDRH5	DDRH4	DDRH3	DDRH2	DDRH1	DDRH0
		W								
0x0263	RDRH	R	RDRH7	RDRH6	RDRH5	RDRH4	RDRH3	RDRH2	RDRH1	RDRH0
		W								
0x0264	PERH	R	PERH7	PERH6	PERH5	PERH4	PERH3	PERH2	PERH1	PERH0
		W								
0x0265	PPSH	R	PPSH7	PPSH6	PPSH5	PPSH4	PPSH3	PPSH2	PPSH1	PPSH0
		W								
0x0266	PIEH	R	PIEH7	PIEH6	PIEH5	PIEH4	PIEH3	PIEH2	PIEH1	PIEH0
		W								
0x0267	PIFH	R	PIFH7	PIFH6	PIFH5	PIFH4	PIFH3	PIFH2	PIFH1	PIFH0
		W								
0x0268	PTJ	R	PTJ7	PTJ6	0	0	0	0	PTJ1	PTJ0
		W								
0x0269	PTIJ	R	PTIJ7	PTIJ6	0	0	0	0	PTIJ1	PTIJ0
		W								
0x026A	DDRJ	R	DDRJ7	DDRJ6	0	0	0	0	DDRJ1	DDRJ0
		W								
0x026B	RDRJ	R	RDRJ7	RDRJ6	0	0	0	0	RDRJ1	RDRJ0
		W								
0x026C	PERJ	R	PERJ7	PERJ6	0	0	0	0	PERJ1	PERJ0
		W								
0x026D	PPSJ	R	PPSJ7	PPSJ6	0	0	0	0	PPSJ1	PPSJ0
		W								
0x026E	PIEJ	R	PIEJ7	PIEJ6	0	0	0	0	PIEJ1	PIEJ0
		W								
0x026f	PIFJ	R	PIFJ7	PIFJ6	0	0	0	0	PIFJ1	PIFJ0
		W								
0x0270	PT0AD0	R	PT0AD07	PT0AD06	PT0AD05	PT0AD04	PT0AD03	PT0AD02	PT0AD01	PT0AD00
		W								
0x0271	PT1AD0	R	PT1AD07	PT1AD06	PT1AD05	PT1AD04	PT1AD03	PT1AD02	PT1AD01	PT1AD00
		W								
0x0272	DDR0AD0	R	DDR0AD07	DDR0AD06	DDR0AD05	DDR0AD04	DDR0AD03	DDR0AD02	DDR0AD01	DDR0AD00
		W								
0x0273	DDR1AD0	R	DDR1AD07	DDR1AD06	DDR1AD05	DDR1AD04	DDR1AD03	DDR1AD02	DDR1AD01	DDR1AD00
		W								
0x0274	RDR0AD0	R	RDR0AD07	RDR0AD06	RDR0AD05	RDR0AD04	RDR0AD03	RDR0AD02	RDR0AD01	RDR0AD00
		W								
0x0275	RDR1AD0	R	RDR1AD07	RDR1AD06	RDR1AD05	RDR1AD04	RDR1AD03	RDR1AD02	RDR1AD01	RDR1AD00
		W								

Appendix F
Ordering Information

F.1 Ordering Information

The following figure provides an ordering part number example for the devices covered by this data book. There are two options when ordering a device. Customers must choose between ordering either the mask-specific part number or the generic / mask-independent part number. Ordering the mask-specific part number enables the customer to specify which particular maskset they will receive whereas ordering the generic maskset means that FSL will ship the currently preferred maskset (which may change over time). In either case, the marking on the device will always show the generic / mask-independent peritoneums and the mask set number.

NOTE

The max length for the part number is 15 characters. Due to this limitation, in some situations, some characters are omitted. The mask identifier suffix and the Tape & Reel suffix are often both omitted from the part number which is actually marked on the device.

For specific part numbers to order, please contact your local sales office. The below figure illustrates the structure of a typical mask-specific ordering number for the S12XS family devices.

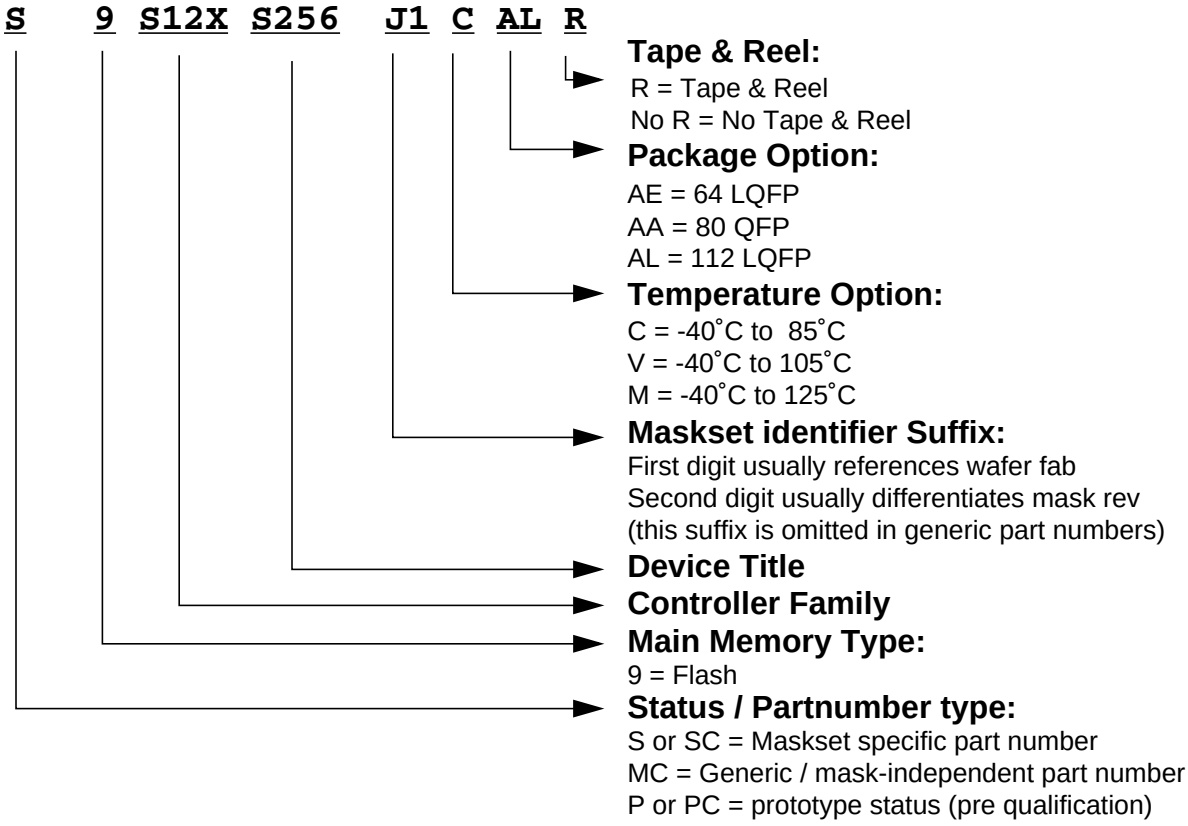


Figure F-1. Order Part Number Example